

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D $T_A = +25^\circ C$
30V	18.6m Ω @ $V_{GS} = 10V$	8.0A
	26.5m Ω @ $V_{GS} = 4.5V$	6.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

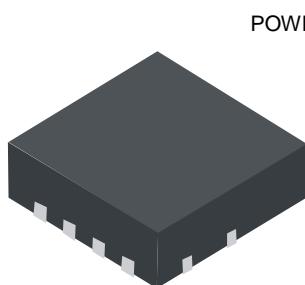
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

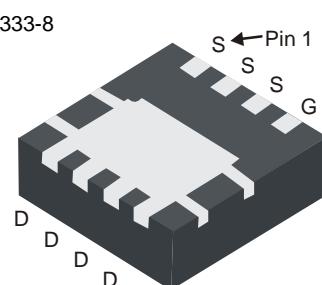
- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) Rated
- 100% R_g Tested
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

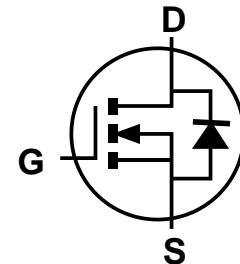
- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)



Top View



Bottom View



Equivalent Circuit

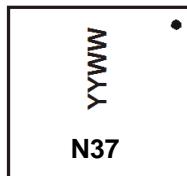
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3027LFG-7	POWERDI [®] 3333-8	2,000 / Tape & Reel
DMN3027LFG-13	POWERDI [®] 3333-8	3,000 / Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N37 = Product Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 15 for 2015)
 WW = Week Code (01 – 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 25	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	5.3 4.2	A
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	8.0 6.3	A
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	$t \leq 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	9.5 7.7	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	6.5 4.9	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	$t \leq 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	7.8 6.2	A
Pulsed Drain Current (Note 7)			I_{DM}	70	A
Avalanche Current (Notes 7 & 8)			I_{AR}	18	A
Repetitive Avalanche Energy (Notes 7 & 8) $L = 0.1\text{mH}$			E_{AR}	16	mJ

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P_D	1.0	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	130.6	°C/W
Power Dissipation (Note 6)	P_D	2.07	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 6)	$R_{\theta JA}$	62.5	°C/W
Power Dissipation (Note 6) $t \leq 10\text{s}$	P_D	3.0	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 6) $t \leq 10\text{s}$	$R_{\theta JA}$	43.8	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:

5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
6. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
7. Repetitive rating, pulse width limited by junction temperature.
8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	-	-	100	nA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.9	1.2	1.8	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	13.5	18.6	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 10\text{A}$
		-	22	26.5		$V_{GS} = 4.5\text{V}, I_D = 7.5\text{A}$
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	-	580	-	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	110	-		
Reverse Transfer Capacitance	C_{rss}	-	70	-		
Gate Resistance	R_g	-	2.0	3.0	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge $V_{GS} = 4.5\text{V}$	Q_g	-	5.3	-	nC	$V_{GS} = 4.5\text{V}, V_{DS} = 15\text{V}, I_D = 10\text{A}$
Total Gate Charge $V_{GS} = 10\text{V}$	Q_g	-	11.3	-		$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}, I_D = 10\text{A}$
Gate-Source Charge	Q_{gs}	-	1.9	-		$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}, I_D = 10\text{A}$
Gate-Drain Charge	Q_{gd}	-	1.9	-		$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}, R_L = 15\Omega, R_G = 6\Omega$
Turn-On Delay Time	$t_{D(ON)}$	-	4.4	-	ns	
Turn-On Rise Time	t_R	-	4.6	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	19.5	-	ns	
Turn-Off Fall Time	t_F	-	5.8	-	ns	

Notes:

9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to production testing.

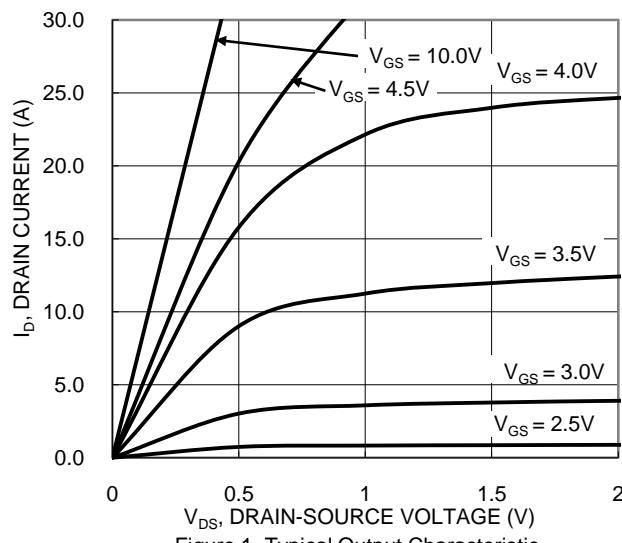


Figure 1. Typical Output Characteristic

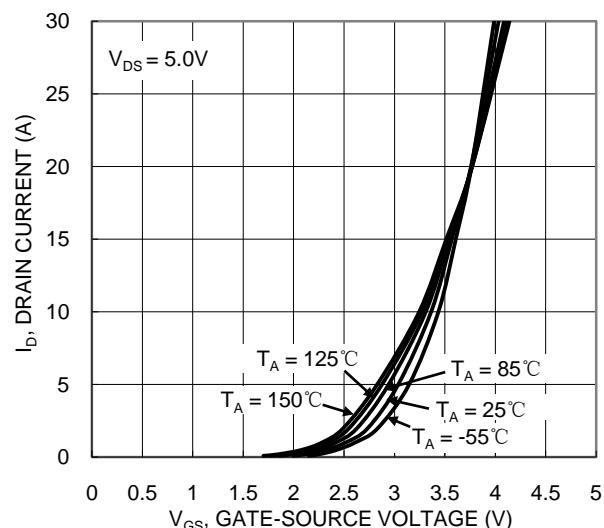


Figure 2. Typical Transfer Characteristic

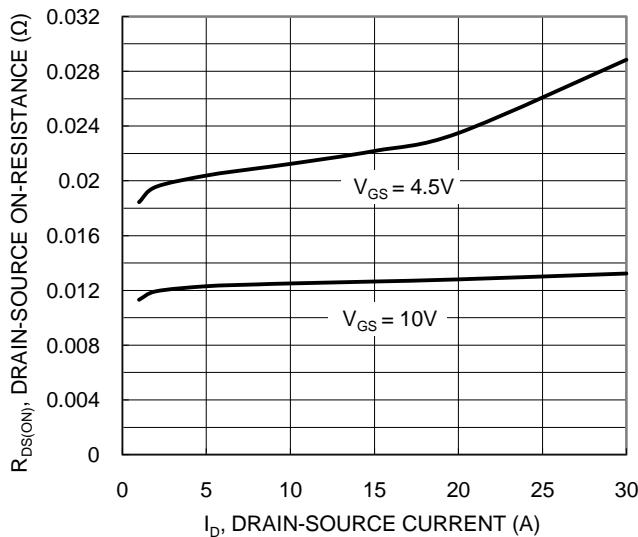


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

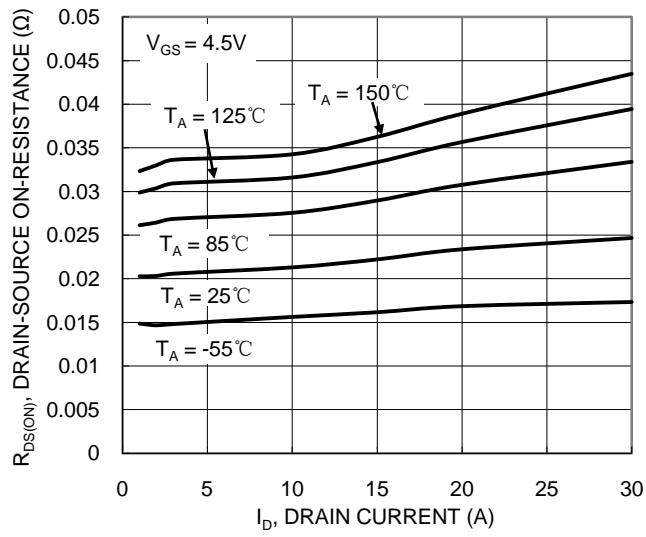


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

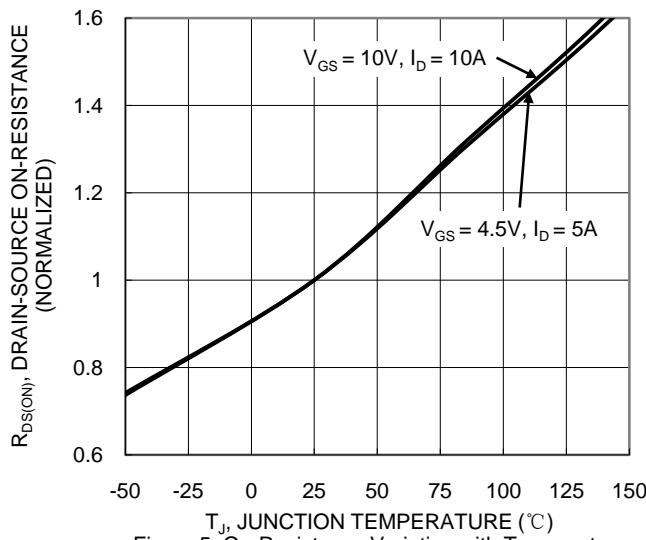


Figure 5. On-Resistance Variation with Temperature

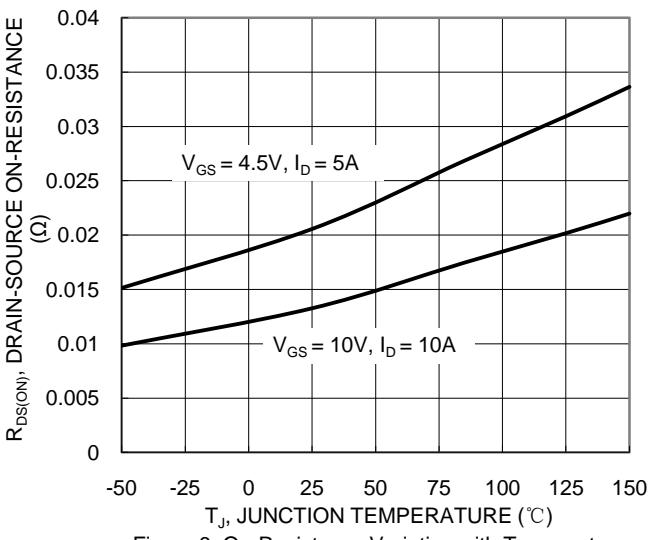


Figure 6. On-Resistance Variation with Temperature

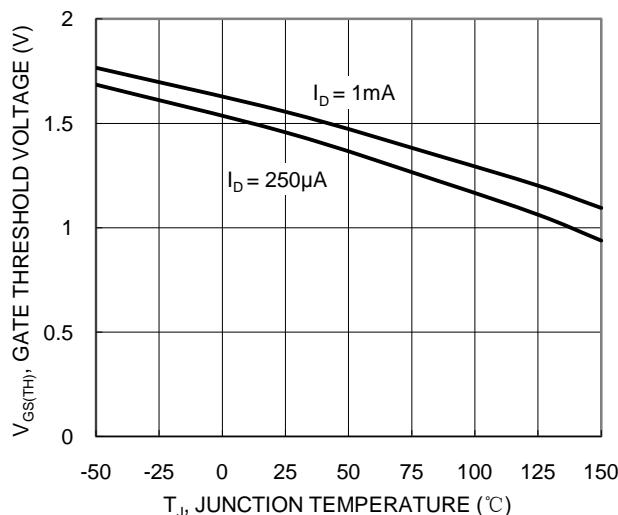


Figure 7. Gate Threshold Variation vs. Temperature

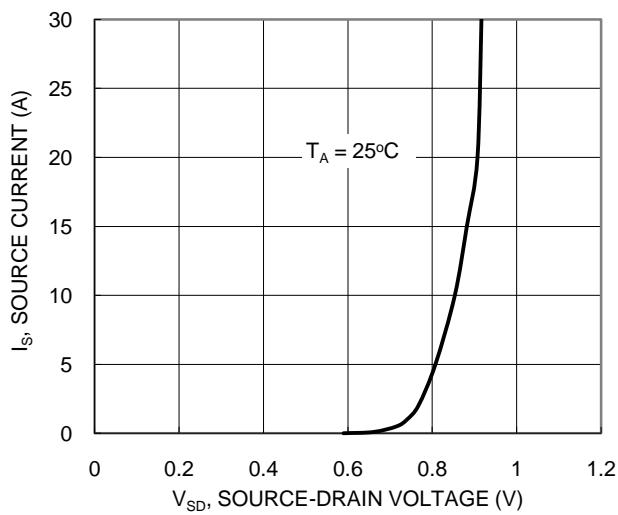


Figure 8. Diode Forward Voltage vs. Current

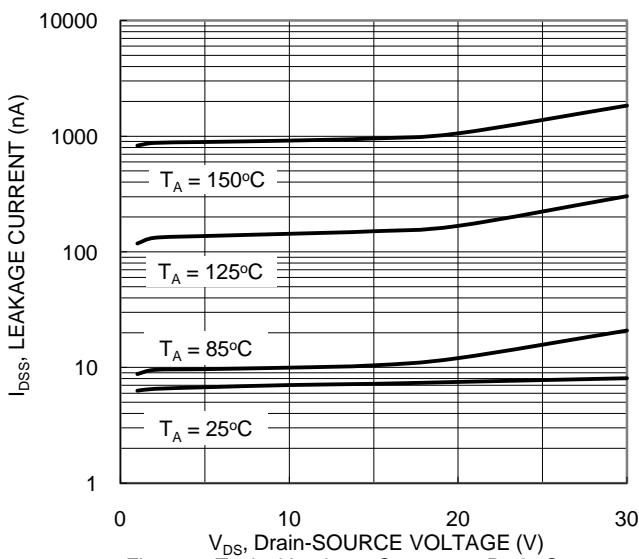


Figure 9. Typical Leakage Current vs. Drain-Source Voltage

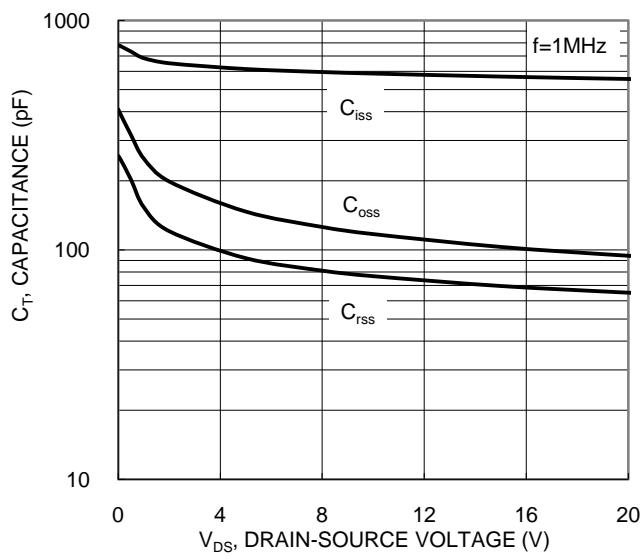


Figure 10. Typical Total Capacitance

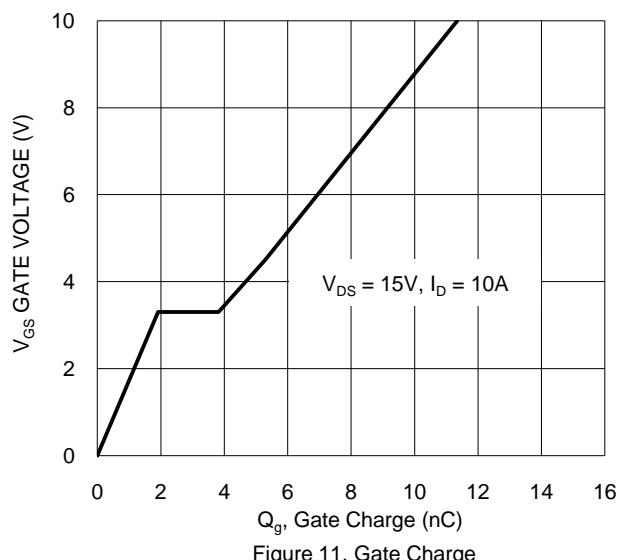


Figure 11. Gate Charge

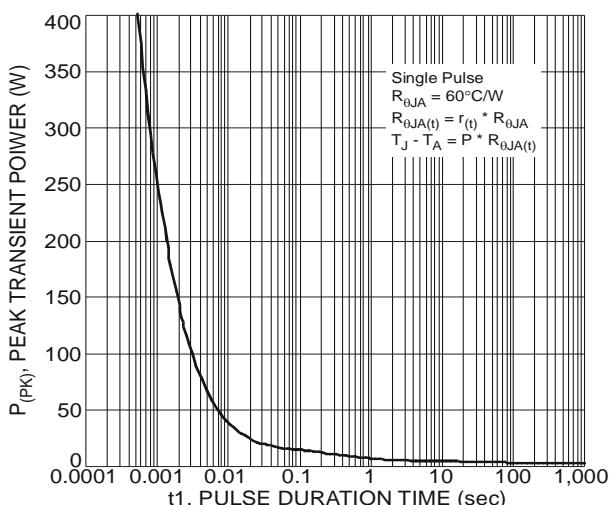
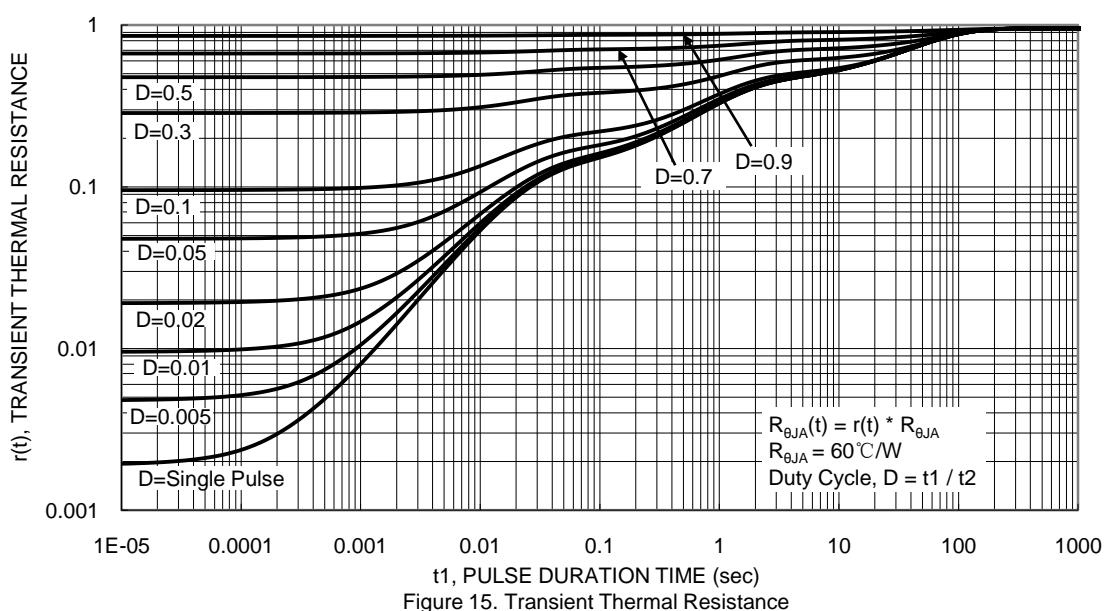
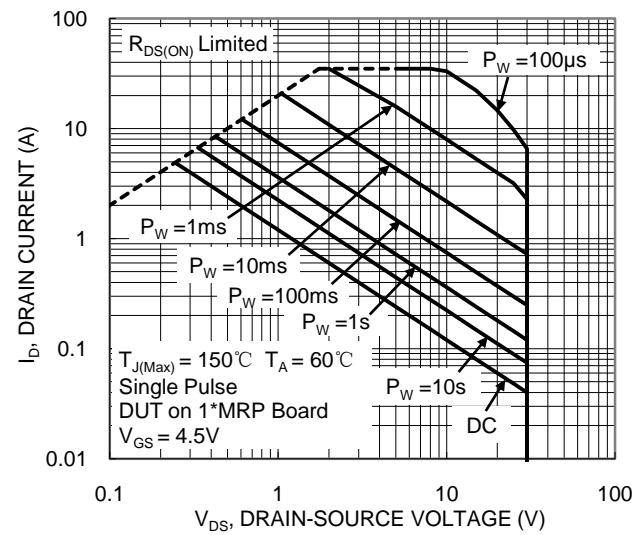
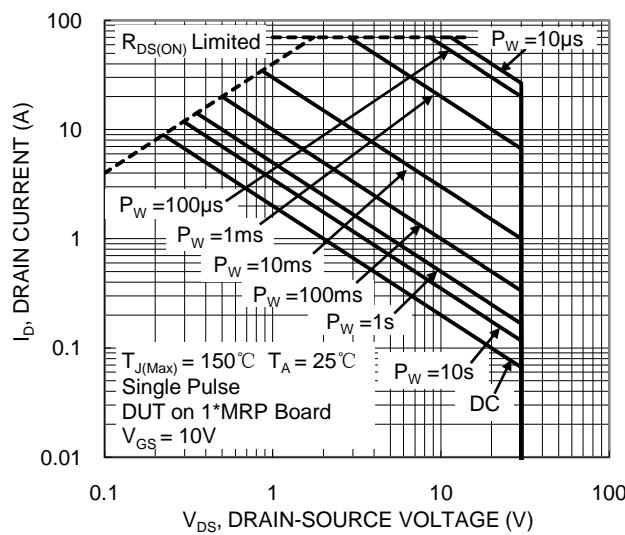


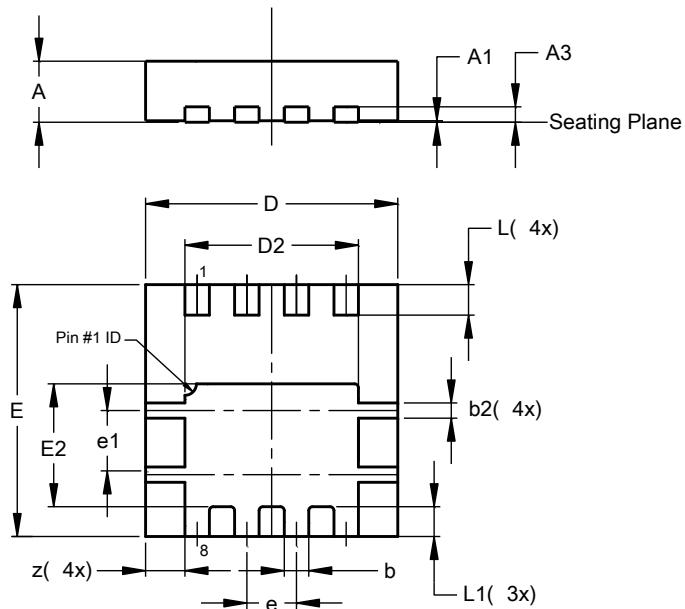
Figure 12. Single Pulse Maximum Power Dissipation



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

POWERDI[®] 3333-8

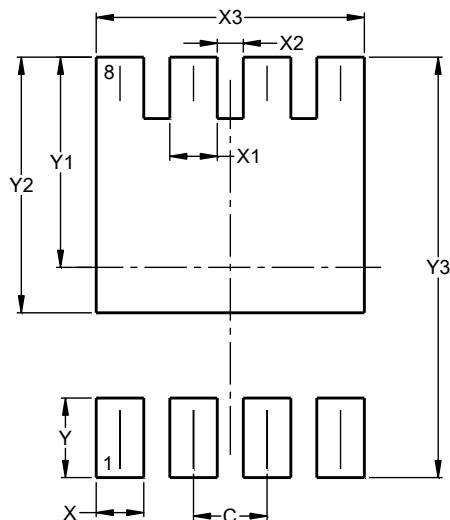


POWERDI [®] 3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

POWERDI[®] 3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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